



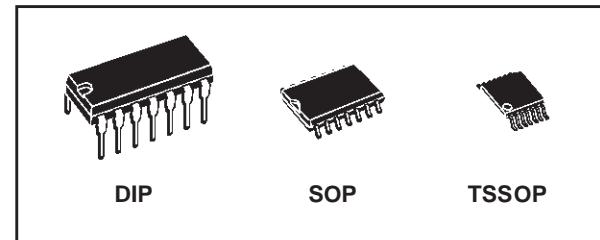
M74HC14

HEX SCHMITT INVERTER

- HIGH SPEED:
 $t_{PD} = 12\text{ns}$ (TYP.) at $V_{CC} = 6\text{V}$
- LOW POWER DISSIPATION:
 $I_{CC} = 1\mu\text{A}$ (MAX.) at $T_A=25^\circ\text{C}$
- HIGH NOISE IMMUNITY:
 $V_H = 1.2\text{ V}$ (TYP.) AT $V_{CC} = 6\text{ V}$
- SYMMETRICAL OUTPUT IMPEDANCE:
 $|I_{OH}| = I_{OL} = 4\text{mA}$ (MIN)
- BALANCED PROPAGATION DELAYS:
 $t_{PLH} \approx t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE:
 V_{CC} (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE WITH
74 SERIES 14

DESCRIPTION

The M74HC14 is an high speed CMOS HEX SCHMITT INVERTER fabricated with silicon gate C²MOS technology. Pin configuration and function are the same as those of the M74HC04 but all inputs have 20% V_{CC} hysteresis level. This, together with its schmitt trigger function, allows it to be used on line receivers with slow rise/fall input signals.

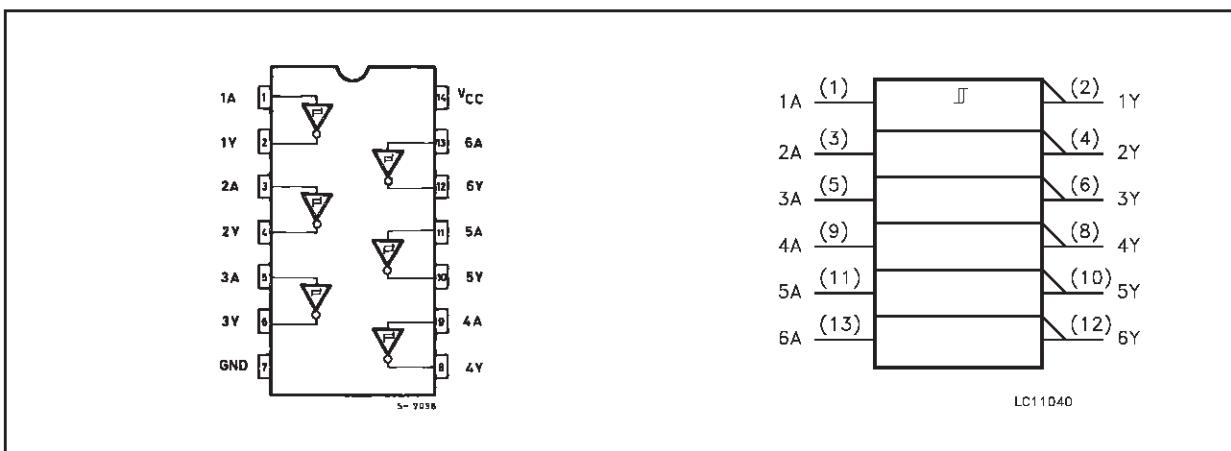


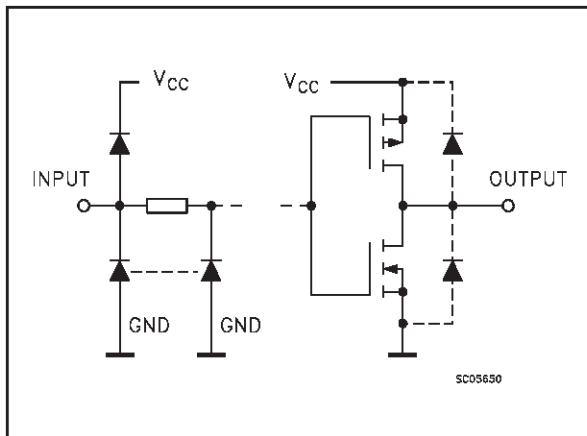
ORDER CODES

PACKAGE	TUBE	T & R
DIP	M74HC14B1R	
SOP	M74HC14M1R	M74HC14RM13TR
TSSOP		M74HC14TTR

All inputs are equipped with protection circuits against static discharge and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



INPUT AND OUTPUT EQUIVALENT CIRCUIT

PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 3, 5, 9, 11, 13	1A to 6A	Data Inputs
2, 4, 6, 8, 10, 12	1Y to 6Y	Data Outputs
7	GND	Ground (0V)
14	V _{CC}	Positive Supply Voltage

TRUTH TABLE

A	Y
L	H
H	L

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7	V
V _I	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
I _O	DC Output Current	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
P _D	Power Dissipation	500(*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

(*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	2 to 6	V
V _I	Input Voltage	0 to V _{CC}	V
V _O	Output Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature	-55 to 125	°C

DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V _{t+}	High Level Input Voltage	2.0		1.0	1.28	1.5	1.0	1.5	1.0	1.5	V
		4.5		2.3	2.8	3.15	2.3	3.15	2.3	3.15	
		6.0		3.0	3.7	4.2	3.0	4.2	3.0	4.2	
V _{t-}	Low Level Input Voltage	2.0		0.3	0.74	0.9	0.3	0.9	0.3	0.9	V
		4.5		1.13	1.8	2.0	1.13	2.0	1.13	2.0	
		6.0		1.5	2.4	2.6	1.5	2.6	1.5	2.6	
V _H	Hysteresis Voltage	2.0		0.3	0.54	1.0	0.3	1.0	0.3	1.0	V
		4.5		0.6	1.0	1.4	0.6	1.4	0.6	1.4	
		6.0		0.8	1.3	1.4	0.8	1.7	0.8	1.7	
V _{OH}	High Level Output Voltage	2.0	I _O =-20 μA	1.9	2.0		1.9		1.9		V
		4.5	I _O =-20 μA	4.4	4.5		4.4		4.4		
		6.0	I _O =-20 μA	5.9	6.0		5.9		5.9		
		4.5	I _O =-4.0mA	4.18	4.31		4.13		4.10		
		6.0	I _O =-5.2 mA	5.68	5.8		5.63		5.60		
V _{OL}	Low Level Output Voltage	2.0	I _O =-20 μA		0.0	0.1		0.1		0.1	V
		4.5	I _O =-20 μA		0.0	0.1		0.1		0.1	
		6.0	I _O =-20 μA		0.0	0.1		0.1		0.1	
		4.5	I _O =-4.0mA		0.17	0.26		0.33		0.40	
		6.0	I _O =-5.2 mA		0.18	0.26		0.33		0.40	
I _I	Input Leakage Current	6.0	V _I = V _{CC} or GND			± 0.1		± 1		± 1	μA
I _{CC}	Quiescent Supply Current	6.0	V _I = V _{CC} or GND			1		10		20	μA

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6ns)

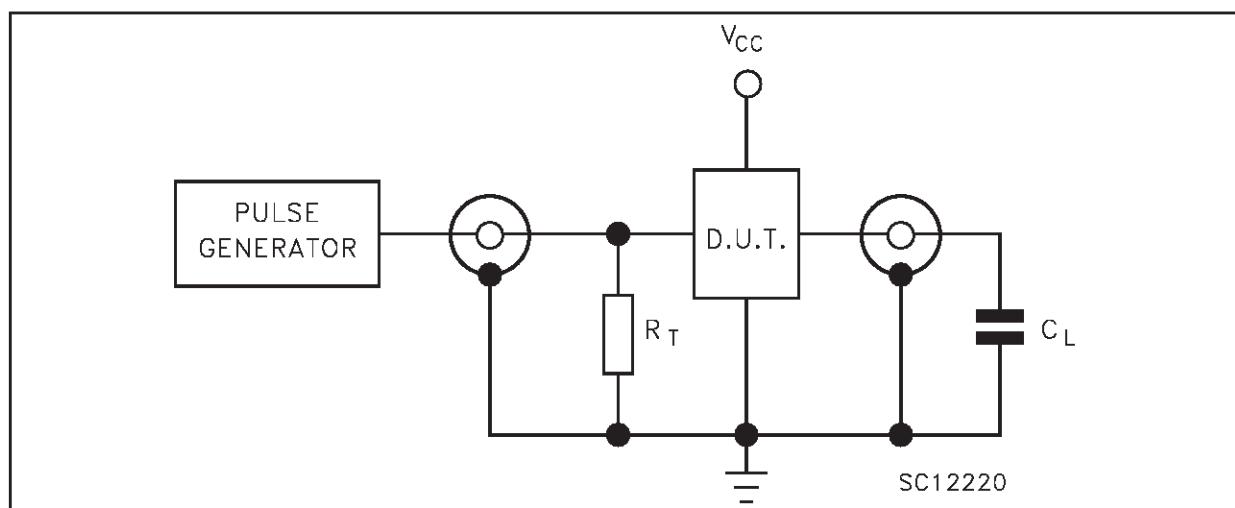
Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t _{TLH} t _{THL}	Output Transition Time	2.0			30	75		95		110	ns
		4.5			8	15		19		22	
		6.0			7	13		16		19	
t _{PLH} t _{PHL}	Propagation Delay Time	2.0			42	125		155		190	ns
		4.5			14	25		31		38	
		6.0			12	21		16		32	

CAPACITIVE CHARACTERISTICS

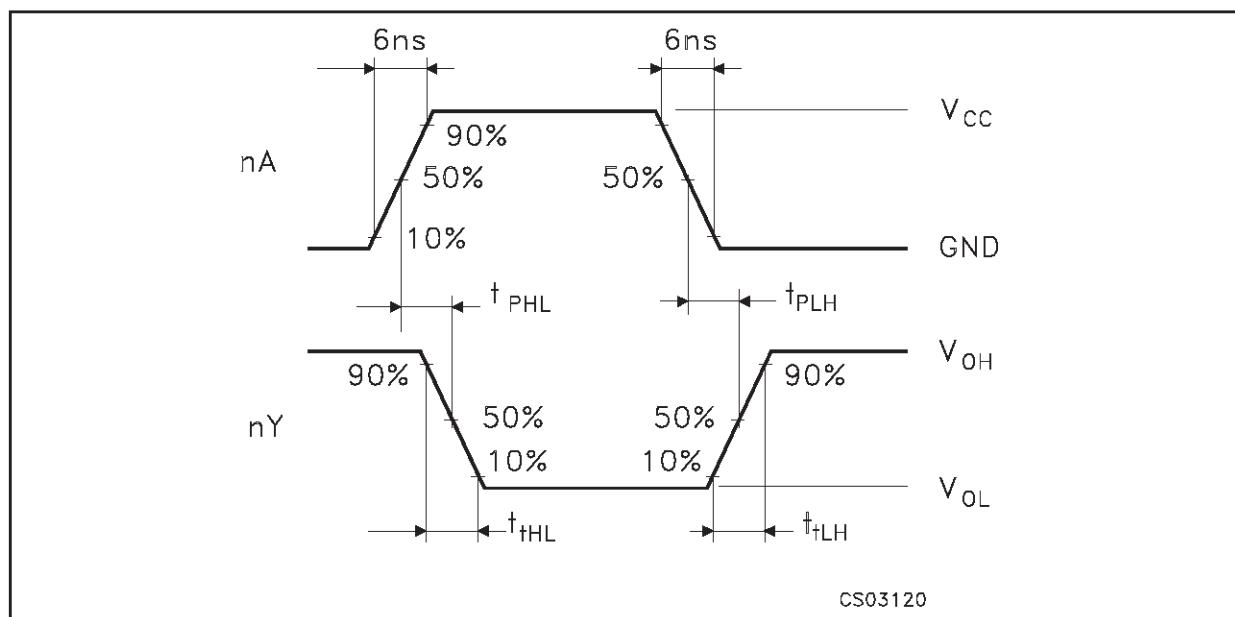
Symbol	Parameter	Test Condition		Value						Unit	
		V_{CC} (V)		$T_A = 25^\circ C$			$-40 \text{ to } 85^\circ C$		$-55 \text{ to } 125^\circ C$		
				Min.	Typ.	Max.	Min.	Max.	Min.		
C_{IN}	Input Capacitance	5.0			5	10		10		10 pF	
C_{PD}	Power Dissipation Capacitance (note 1)	5.0	$f_{IN} = 10\text{MHz}$		28					pF	

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(\text{opr})} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/6(\text{per gate})$

TEST CIRCUIT

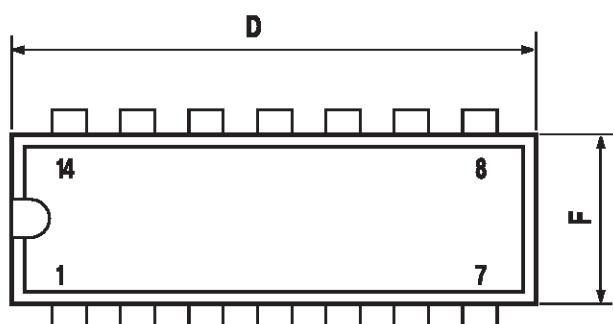
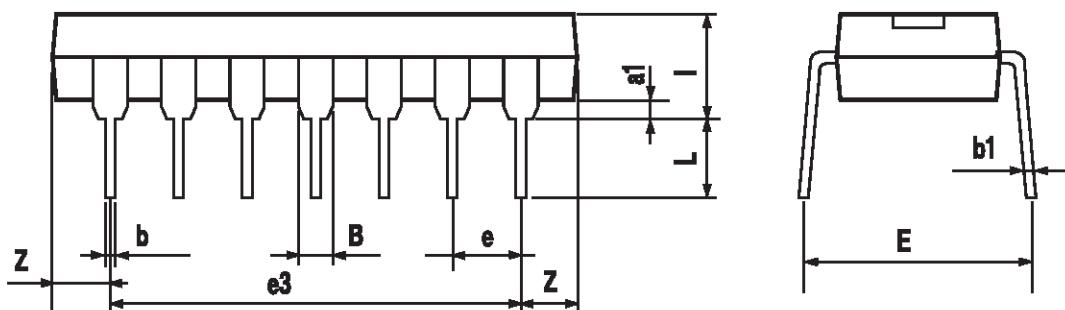


$C_L = 50\text{pF}$ or equivalent (includes jig and probe capacitance)
 $R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

WAVEFORM : PROPAGATION DELAY TIMES ($f=1\text{MHz}$; 50% duty cycle)

Plastic DIP-14 MECHANICAL DATA

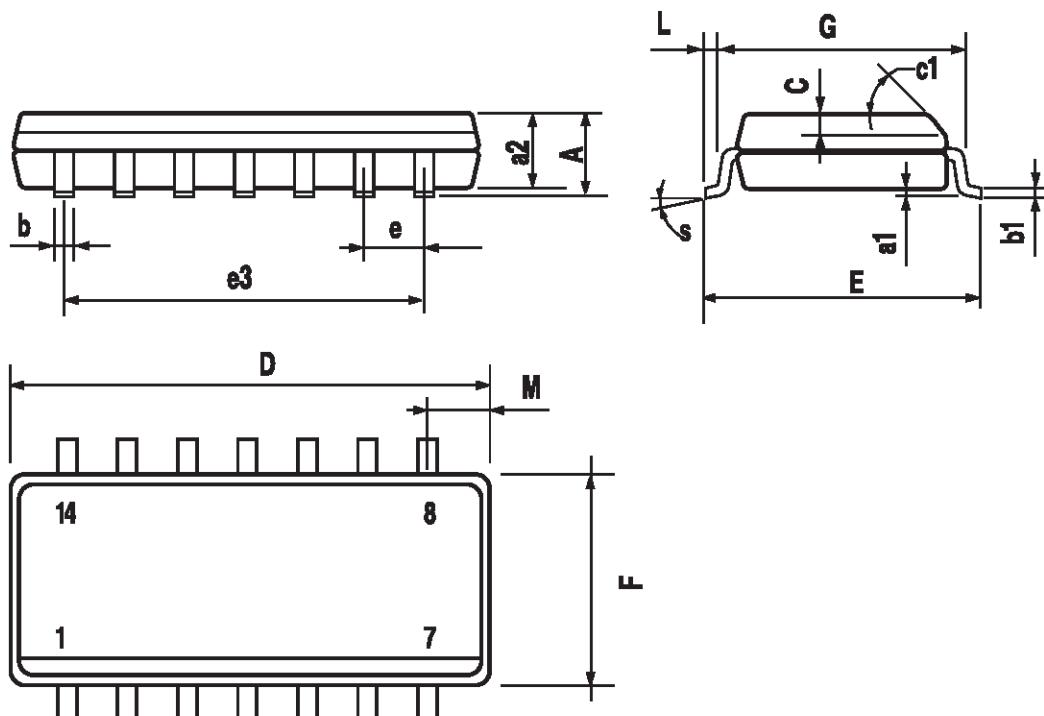
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



P001A

SO-14 MECHANICAL DATA

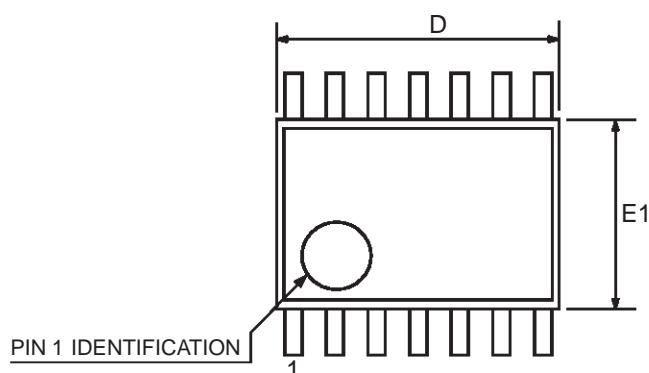
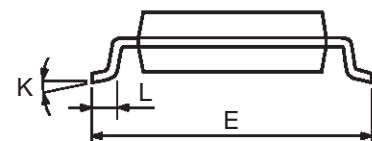
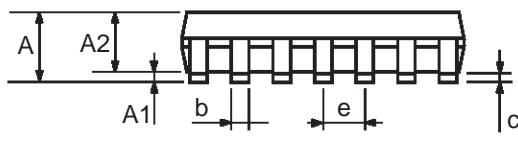
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



PO13G

TSSOP14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	4.9	5	5.1	0.193	0.197	0.201
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



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